Abstract

Method for identifying an incorrect position of a semiconductor wafer during a thermal treatment

The invention relates to a method for identifying an incorrect position of a semiconductor wafer during a thermal treatment in a process chamber which is heated by means of infrared emitters and is transmissive to infrared radiation, wherein the semiconductor wafer lies in a circular pocket of a rotating susceptor and is held at a predetermined temperature with the aid of the infrared emitters and a control system, and wherein thermal radiation is measured by means of a pyrometer, an amplitude of the fluctuations of the measurement signal is determined and an incorrect position of the semiconductor wafer is assumed if the amplitude exceeds a predetermined maximum value. In this case, the pyrometer is oriented in such a way that the measurement spot detected by the pyrometer lies partly on the semiconductor wafer and partly outside the semiconductor wafer on the susceptor. In this way, it is possible to identify an eccentric position of the semiconductor wafer within the pocket of the susceptor.

Fig. 4